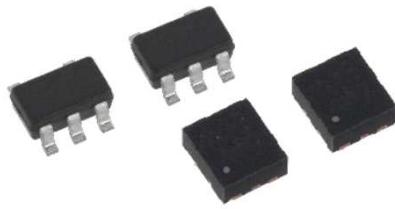


200mA Negative LDO

MM1998 Series



Overview

This IC is a negative output 200mA LDO with fast turn-on by bipolar process.

The target applications are a negative power supply for highly sensitive CMOS image sensor by low noise design.

And The IC has the line-up of output voltage -5.0V to -1.1V (0.1V steps) by the specifications of image sensor.

The package can be selected from SOT-25/SSON-6A for low cost or small space of PCB.

Overview

- ON/OFF control
- Noise reduction capacitor
- C_n charge-up circuit

Main specifications

- | | |
|---------------------------------|--|
| ■ Maximum rating supply voltage | : -12V to 0.3V |
| ■ Operating voltage range | : -10V to -2V |
| ■ Operating ambient temperature | : -40°C to 85°C |
| ■ Output current | : 200mA |
| ■ Input current (OFF) | : Typ. 4uA |
| ■ No-load input current | : Typ. 160uA |
| ■ Output voltage range | : -5.0V to -1.1V (0.1V step) |
| ■ Output voltage accuracy | : ±1.0% ($V_{OUT}(\text{Typ.}) \leq -1.5V$)
±15mV ($V_{OUT}(\text{Typ.}) > -1.5V$) |
| ■ Line regulation | : Typ. 0.01%/V ($V_{EE}=V_{OUT}(\text{Typ.})-1V$ to -10V) |
| ■ Load regulation | : Typ. 15mV ($I_{OUT}=1\text{mA}$ to 200mA) |
| ■ Dropout voltage | : Typ. 0.5V ($I_{OUT}=200\text{mA}$) |
| ■ PSRR | : Typ. 70dB (f=1kHz) |
| ■ Output noise voltage | : Typ. 25uVrms ($f_{BW}=10$ to 100kHz, $I_{OUT}=10\text{mA}$, $V_{OUT}(\text{Typ.})=-1.4V$) |
| ■ Output capacitor | : 1uF (Ceramic capacitor) |
| ■ Protection function | : Over current protection, Thermal shutdown |
| ■ Additional function | : ON/OFF control, Auto discharge, |

Packages

- SSON-6A
- SOT-25A

Application

- Photographing / Imaging device
- Power supply for high-sensitivity image sensor
- Power supply for negative voltage circuit



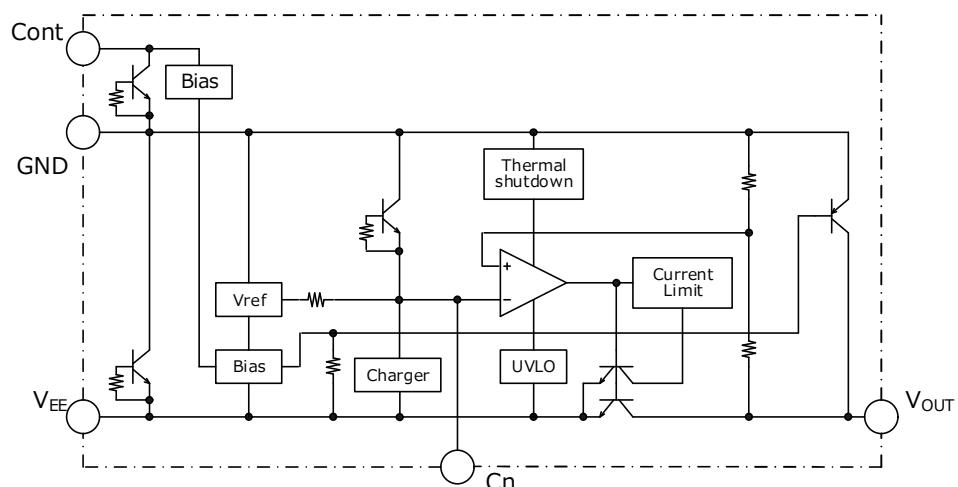
Model Name

M M 1 9 9 8 A X X X X X

Series name (A) (B) (C) (D) (E)

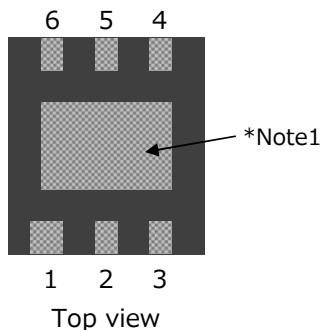
(A)	Function Type	A	Cont=H active
(B)	Output voltage rank	11	Output voltage can be designated in the range from -1.1V(11) to -5.0V(50) in 0.1V steps.
		?	
		50	
(C)	Package	R	SSON-6A
		N	SOT-25A
(D)	Packing specifications 1	R	R housing (Standard)
		L	L housing
(E)	Packing specifications 2	E	Emboss tape / Halogen free (SSON-6A)
		E	Emboss tape / Halogen contained (SOT-25A)

Block Diagram



Pin Configuration

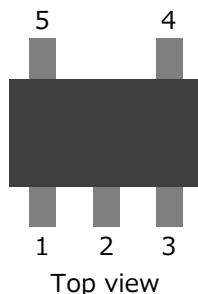
■ SSON-6A



Pin No.	Pin name	Function
1	Cont	Control pin Vcont=H : Output ON Vcont=L : Output OFF
2	GND	GND pin
3	V _{EE}	Negative voltage input pin
4	V _{OUT}	Negative voltage output pin
5	NC	No connection pin
6	Cn	Reducing noise pin with capacitor

*Note1:Heat spreader bottom with VEE. Not connect to GND.

■ SOT-25A



Pin No.	Pin name	Function
1	GND	GND pin
2	V _{EE}	Negative voltage input pin
3	Cont	Control pin Vcont=H : Output ON Vcont=L : Output OFF
4	Cn	Reducing noise pin with capacitor
5	V _{OUT}	Negative voltage output pin

Absolute Maximum Ratings

Item	Symbol	Min.	Max.	Unit
Storage temperature	T _{stg}	-55	125	V
Junction temperature	T _j _{MAX}	-	125	V
Supply voltage	V _{EE}	-12	0.3	V
Cont input voltage	V _{cont}	-0.3	5.0	V
Output current	I _{OUT} _{max}	0	400	mW
Power dissipation	SSON-6A	Pd1	-	1000 mW
*Note2	SOT-25A		-	560 mW

*Note2:JEDEC51-7 standard

Recommended Operating Conditions

Item	Symbol	Min.	Max.	Unit
Operating ambient temperature	T _{opr}	-40	85	°C
Operating voltage	V _{op}	-10	-2.0	V
Output current	I _{op}	0	200	mA

Electrical Characteristics

(V_{EE}=V_{OUT}(Typ.)-1V, V_{cont}=1.6V, I_{OUT}=1mA, Ta=25°C unless otherwise specified)

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit
Input current (OFF)	I _{EEoff}	V _{EE} =-5V, V _{cont} =0V	-	4	8.0	µA
No-Load input current	I _{EE}	I _{OUT} =0mA	-	160	240	µA
Output voltage *Note3	V _{OUT}	V _{OUT} ≤-1.5V	×1.01	-	×0.99	V
		V _{OUT} >-1.5V	-0.015	-	+0.015	V
Dropout voltage	V _{io}	V _{EE} =V _{OUT} +0.2V, I _{OUT} =200mA	-	0.5	0.8	V
Line regulation	V _{LINE}	V _{EE} =V _{OUT} (Typ.)-1V to -10V	-	0.01	0.10	%/V
Load regulation	V _{LOAD}	1mA≤I _{OUT} ≤200mA	-	15	100	mV
Vout temperature coefficient *Note4	ΔV _{OUT} /ΔT _{OP}	-40≤Ta≤85°C	-	±100	-	ppm/°C
Ripple rejection *Note4	RR	f=1kHz, Vripple=0.5V I _{OUT} =10mA, C _n =0.01µF	-	70	-	dB
Output noise voltage *Note4	V _n	V _{OUT} =-1.4V, fBW=10~100kHz, I _{OUT} =10mA, C _n =0.01µF	-	25	-	µVrms

*Note3:Please refer to another page.

*Note4:The parameter is guaranteed by design.

Electrical Characteristics

($V_{EE}=V_{OUT}(\text{Typ.})-1\text{V}$, $V_{cont}=1.6\text{V}$, $I_{OUT}=1\text{mA}$, $Ta=25^\circ\text{C}$ unless otherwise specified)

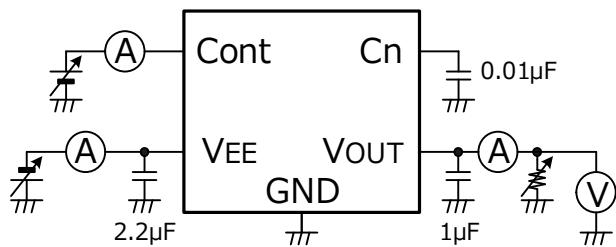
Item	Symbol	Conditions	Min.	Typ.	Max.	Unit
Cont pin input current	I_{cont}	$V_{cont}=1.6\text{V}$	-	4	12	μA
Cont pin High Threshold level	V_{contH}		1.2	-	-	V
Cont pin Low Threshold level	V_{contL}		-	-	0.3	V
Output rise time	t_{short}	$C_n=0.01\mu\text{F}$, $I_{OUT}=0\text{mA}$ *Note5	-	0.17	-	ms
UVLO detective voltage	V_{UVLO}		-1.85	-1.75	-1.65	V
UVLO hysteresis voltage	ΔV_{UVLO}		-	0.15	-	V
Discharge current	I_{dis}	$V_{EE}=-5\text{V}$, $V_{cont}=0\text{V}$	-	4.0	-	mA

*Note4:The parameter is guaranteed by design.

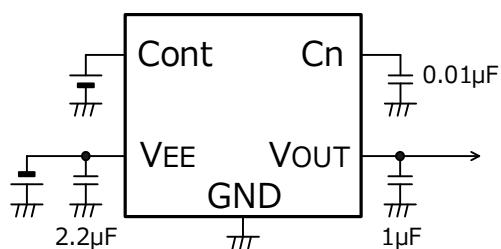
*Note5: $V_{cont}=H$ to 90% of $V_{out}(\text{Typ.})$

Model name	Conditions	Output voltage [V]			Model name	Conditions	Output voltage [V]		
		Min.	Typ.	Max.			Min.	Typ.	Max.
MM1998A11	$I_{OUT}=1\text{mA}$	-1.115	-1.100	-1.085	MM1998A31	$I_{OUT}=1\text{mA}$	-3.131	-3.100	-3.069
MM1998A12		-1.215	-1.200	-1.185	MM1998A32		-3.232	-3.200	-3.168
MM1998A13		-1.315	-1.300	-1.285	MM1998A33		-3.333	-3.300	-3.267
MM1998A14		-1.415	-1.400	-1.385	MM1998A34		-3.434	-3.400	-3.366
MM1998A15		-1.515	-1.500	-1.485	MM1998A35		-3.535	-3.500	-3.465
MM1998A16		-1.616	-1.600	-1.584	MM1998A36		-3.636	-3.600	-3.564
MM1998A17		-1.717	-1.700	-1.683	MM1998A37		-3.737	-3.700	-3.663
MM1998A18		-1.818	-1.800	-1.782	MM1998A38		-3.838	-3.800	-3.762
MM1998A19		-1.919	-1.900	-1.881	MM1998A39		-3.939	-3.900	-3.861
MM1998A20		-2.020	-2.000	-1.980	MM1998A40		-4.040	-4.000	-3.960
MM1998A21		-2.121	-2.100	-2.079	MM1998A41		-4.141	-4.100	-4.059
MM1998A22		-2.222	-2.200	-2.178	MM1998A42		-4.242	-4.200	-4.158
MM1998A23		-2.323	-2.300	-2.277	MM1998A43		-4.343	-4.300	-4.257
MM1998A24		-2.424	-2.400	-2.376	MM1998A44		-4.444	-4.400	-4.356
MM1998A25		-2.525	-2.500	-2.475	MM1998A45		-4.545	-4.500	-4.455
MM1998A26		-2.626	-2.600	-2.574	MM1998A46		-4.646	-4.600	-4.554
MM1998A27		-2.727	-2.700	-2.673	MM1998A47		-4.747	-4.700	-4.653
MM1998A28		-2.828	-2.800	-2.772	MM1998A48		-4.848	-4.800	-4.752
MM1998A29		-2.929	-2.900	-2.871	MM1998A49		-4.949	-4.900	-4.851
MM1998A30		-3.030	-3.000	-2.970	MM1998A50		-5.050	-5.000	-4.950

Test Circuit



Application Circuit

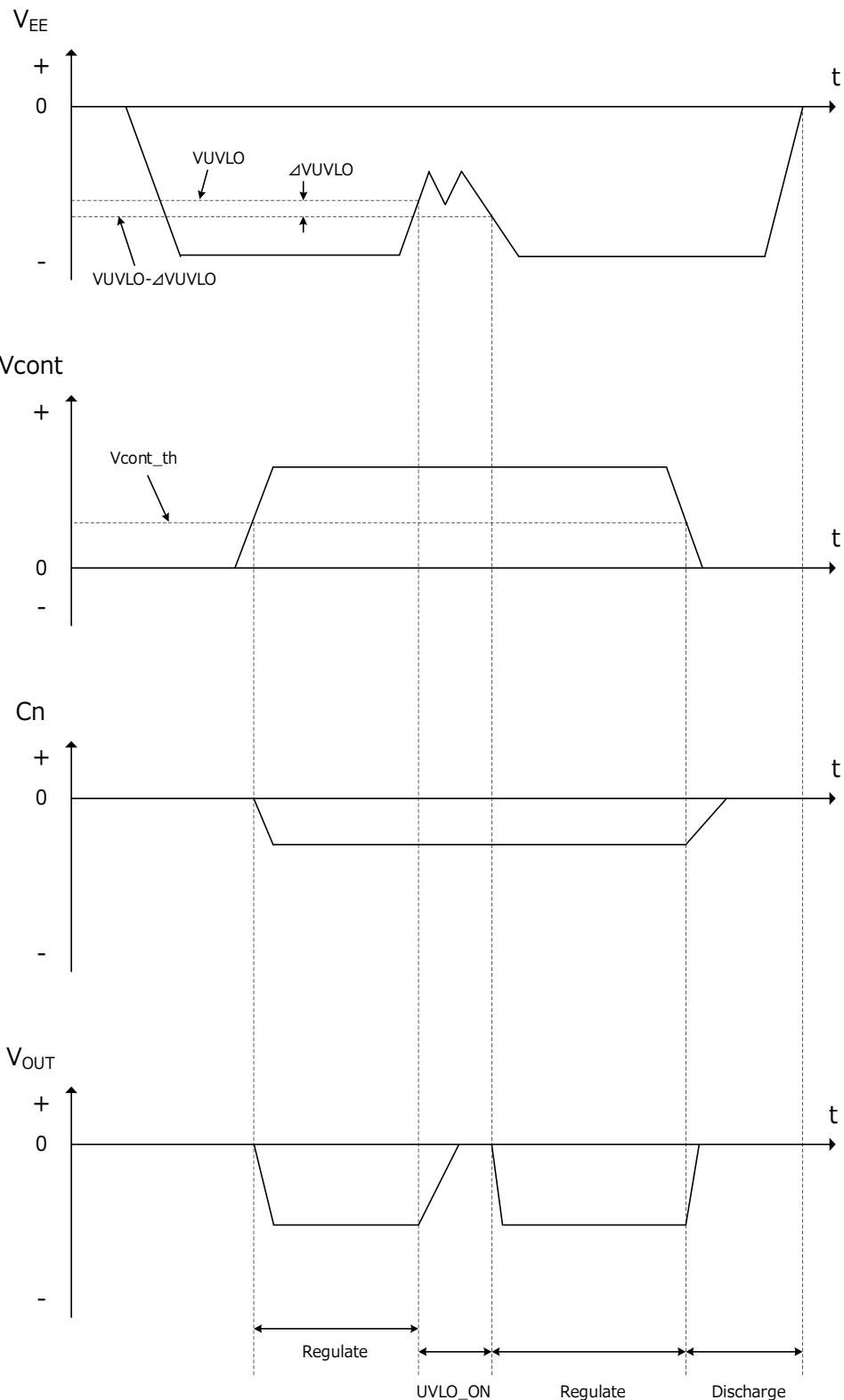


(Example of external parts)

- Output capacitor Ceramic capacitor 1.0μF($V_{OUT} \geq -1.3V$):2.2μF
- Input capacitor Ceramic capacitor 2.2μF *Temperature characteristics : B

- In the event a problem which may affect industrial property or any other rights of us or a third party is encountered during the use of information described in these circuit, we shall not be liable for any such problem, nor grant a license therefore.

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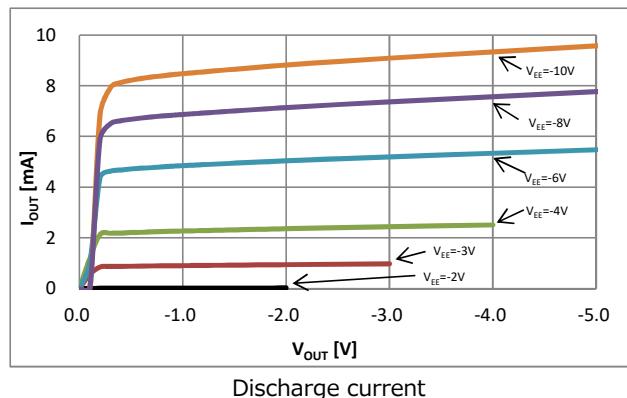


Discharge current depending ON power supply

Discharge current depend on power supply VEE.

Reference to Below current characteristics.

In case of discharge current being low, contact us.



Discharge circuit current

Discharge current is collector current of discharge element in IC.

Collector current I_c is h_{FE} times as many as base current I_b , equation (1).

Base current I_b depend on bias resistance R , equation (2).

Collector current express equation (3).

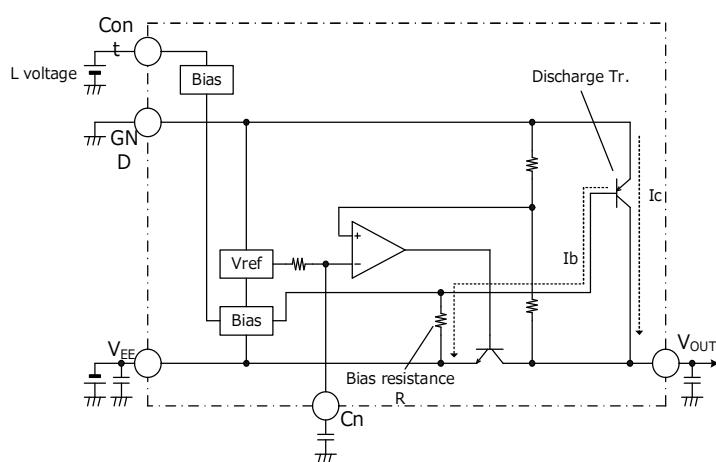
Discharge current (collector current) depend on VEE voltage.

And base current is input current (OFF).

$$I_c = h_{FE} \times I_b \quad \dots(1)$$

$$I_b = (V_{EE} - 0.7) \div R \quad \dots(2)$$

$$I_c = h_{FE} \times (V_{EE} - 0.7) \div R \quad \dots(3)$$



Cn pin

Cn pin is connected with resistance 165k Ω in IC.

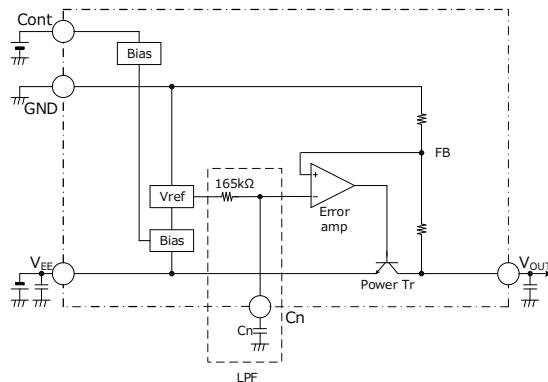
LPF is composed of capacitor, Cn noise is reduced and Vout noise is reduced too.

This IC feedback FB that is divided from Vout by resistance equal with Cn voltage.

Noise of FB is feedbacked equal with noise of Cn too.

So noise of Vout depend on noise of Cn. The capacitor of Cn pin more than 0.01uF is recommended.

If Cn pin influence by noise for outside, noise of Vout pin is bad characteristics.



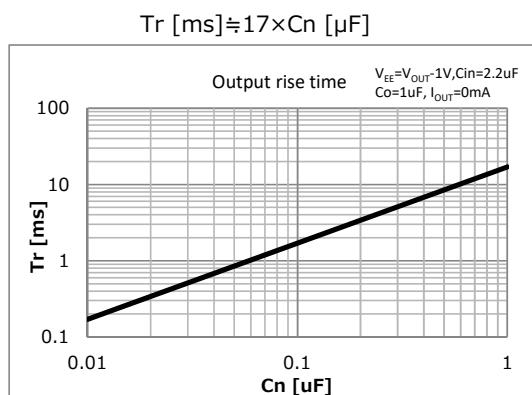
Output rise time

MM1998 rise time Tr in depend on capacitor connected with Cn pin.

Cn voltage start when current from charge up circuit flow to capacitor.

FB voltage is feedback equal to Cn voltage, therefore FB and Vout voltage start.

About output rise time, refer to below equation and characteristics.



Note

1. There is a possibility with deterioration and destruction of IC when using it exceeding the absolute maximum rating.

The absolute maximum rating , Never exceed it.
The functional operation is not assured.

2. There is a possibility that it becomes impossible to maintain this performance and reliability IC original when using it exceeding recommended operation voltage.
Please use it in recommended operation voltage.

3. Due to restrictions on the package power dissipation, the output current value may not be satisfied. Attention should be paid to the power dissipation of the package when the output current is large or the voltage between Input and Output is high.

4. The output capacitor is required between output and GND to prevent oscillation.

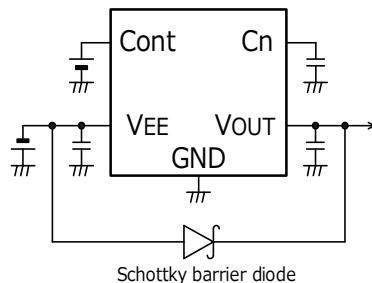
5. The ESR of capacitor must be defined in ESR stability area.

It is possible to use a ceramic capacitor without ESR resistance for output.
The ceramic capacitor must be used more than $1.0\mu F$ and B temperature characteristics.
The ceramic capacitor must be used more than $2.2\mu F$ and B temperature characteristics for $V_o \geq -1.3V$.

6. The wire of VEE and GND is required to print full ground plane for noise and stability.

7. The input capacitor must be connected a distance of less than 1cm from input pin.

8. In case the output voltage is above the input voltage, the overcurrent flow by internal parasitic diode from output to input. In such application, the external bypass diode must be connected between output and input pin.



9. It is able to an unstable operation when you use the capacitor with intense capacitance change
The capacitor has the dependency at the power-supply voltage and the temperature.
The capacity value changes by the environment used. Please evaluate IC in the set.

10. The IC has the thermal shutdown protection.

Note

11. This IC will limit the output current with the overcurrent protection circuit when the overcurrent and the output do short-circuit.

However, IC generates heat because of the substrate and use conditions and there is a possibility of destroying it exceeding a permissible loss.

The characteristic changes depending on the substrate condition.

Please evaluate IC in the set.

12. Cont pin control ON/OFF of this IC. Cont pin is used to input plus voltage.

If this pin is open, this IC is OFF.

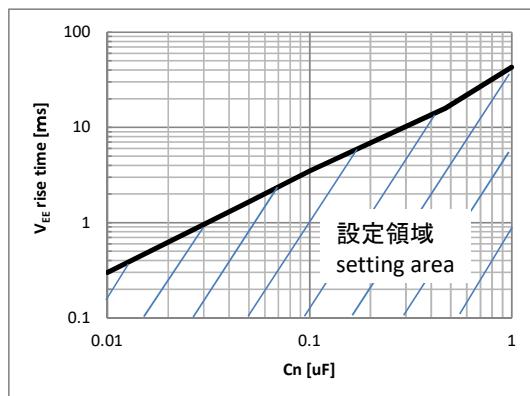
ON : $+1.2V \leq V_{cont} \leq +5.0V$

OFF : $0V \leq V_{cont} \leq +0.3V$

13. The overshoot might be generated in UVLO releasing for low output voltage rank.

It is above function When VEE rise time is late and strating by not Cont but VEE

So set the setting area in below graf.

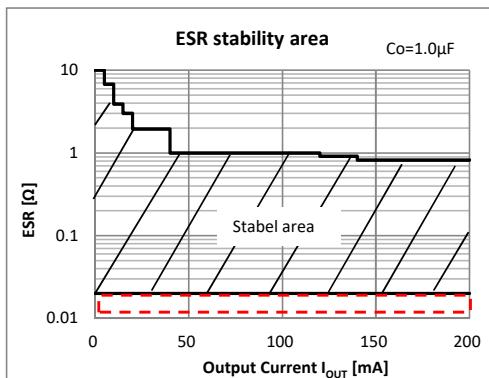


14. It is no data in under 0.02Ω of ESR characteristics.(dotted line area)

Don't be measured in this area because ceramic capacitor contain 0.02Ω in parts self.

Ceramic capacitor only can be used without ESR resistance parts.

Please evaluate IC in the set if the capacitor that is low resistance used.



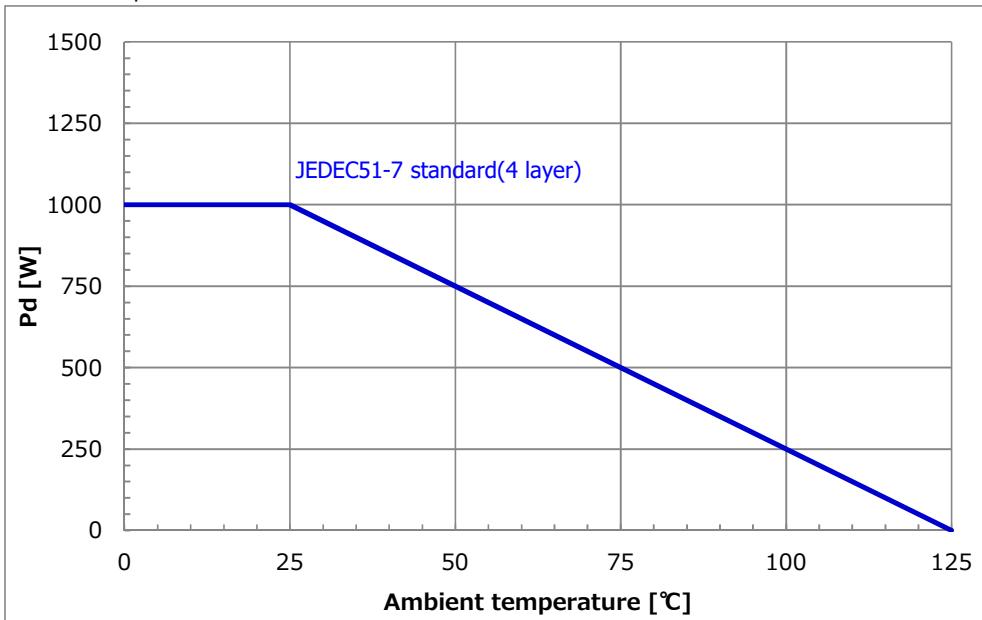
許容損失について

The Power dissipation change if board to mount IC change because radiative heat fix at board.
It is reference data below, Evaluate IC in the set.

■ SSON-6A

1. JEDEC51-7 standard (4 layer FR-4 board)

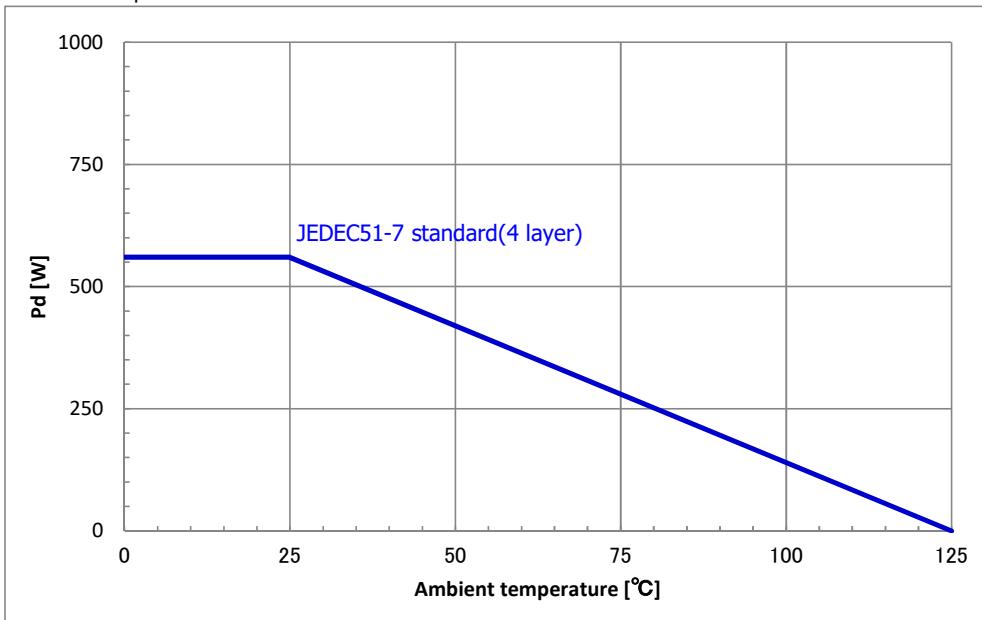
Board size 114.3mm×76.2mm t=1.6mm Copper foil area 80%
Power dissipation 1000mW Ta=25°C



■ SOT-25A

1. JEDEC51-7 standard (4 layer FR-4 board)

Board size 114.3mm×76.2mm t=1.6mm Copper foil area 80%
Power dissipation 560mW Ta=25°C

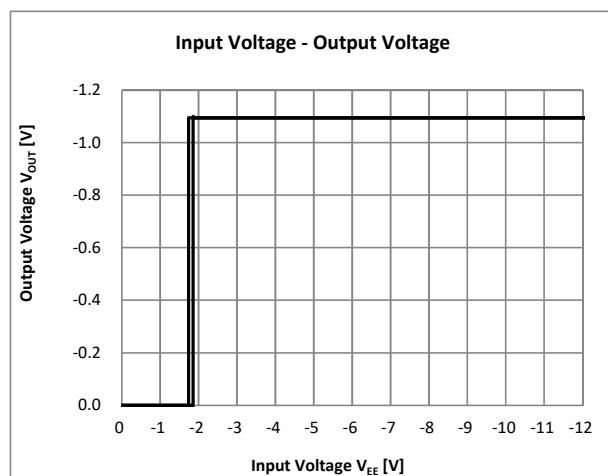
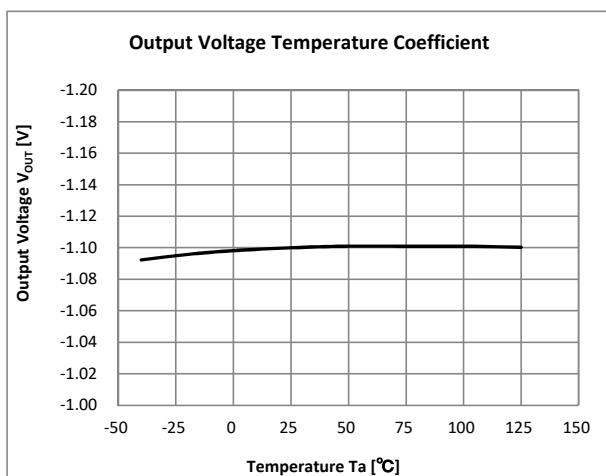
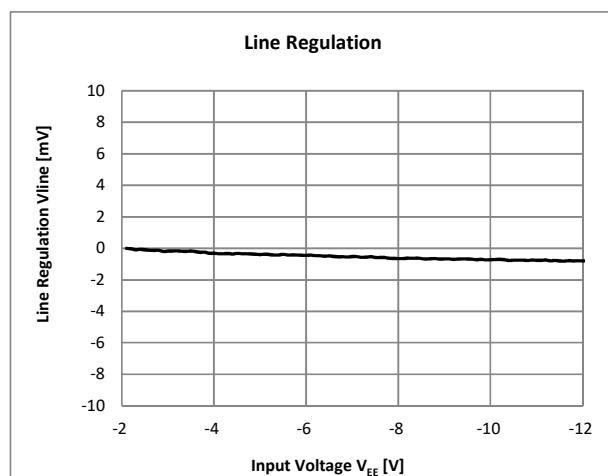
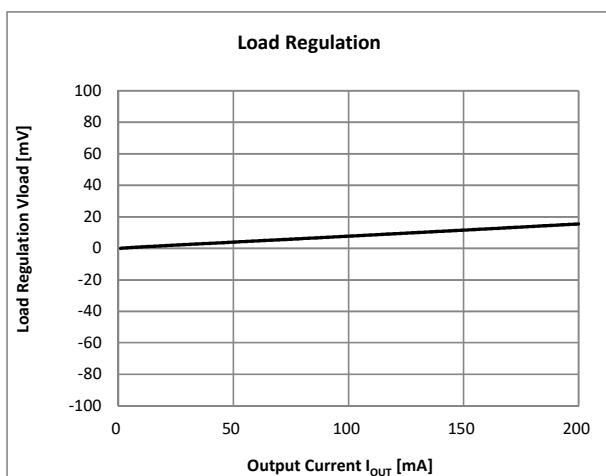
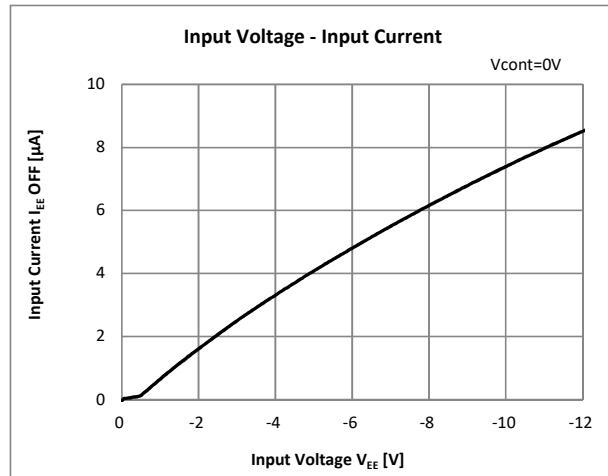
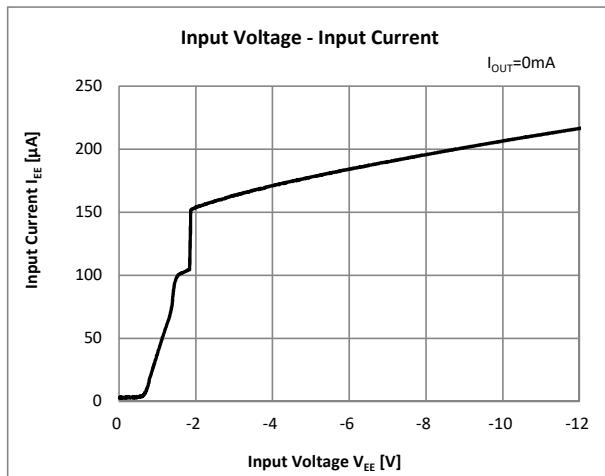


It is recommended to layout the VIA for heat radiation in the GND pattern of reverse (of IC) when there is the GND pattern in the inner layer (in using multiplayer substrate).

By increasing these copper foil pattern area of PCB, Power dissipation improves.

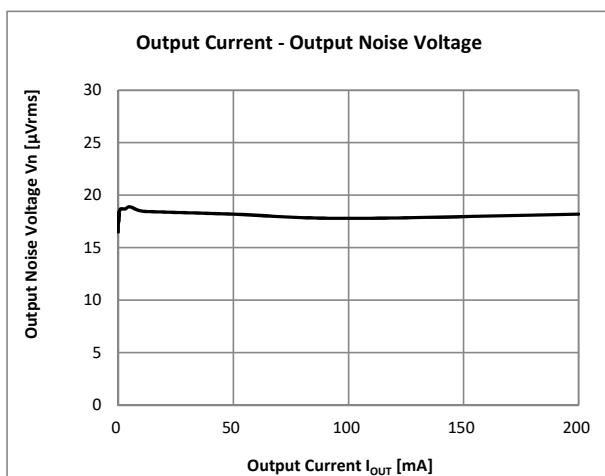
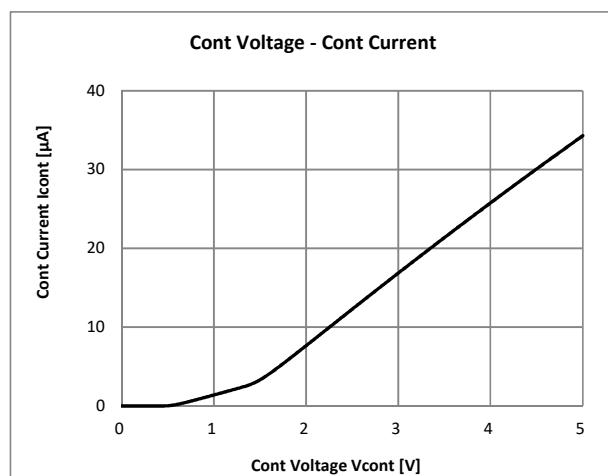
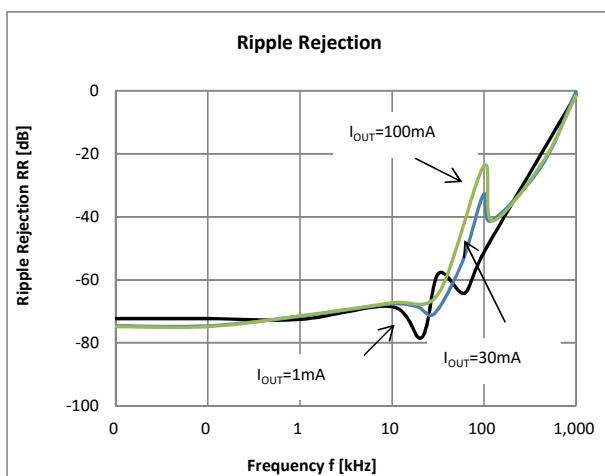
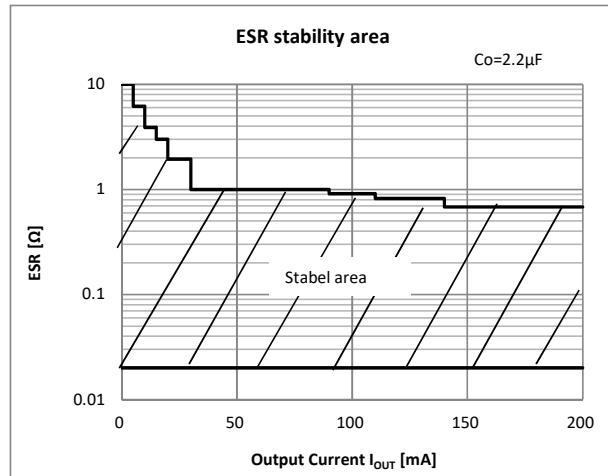
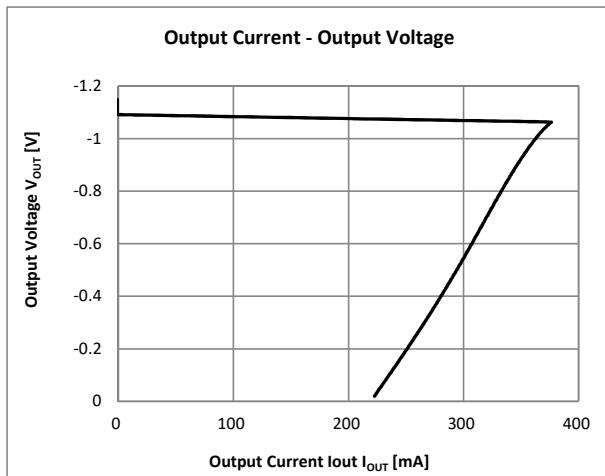
Typical Performance Characteristics ($V_{OUT}=-1.1V$)

($V_{EE}=V_{OUT}(\text{Typ.})-1V$, $V_{cont}=1.6V$, $I_{OUT}=1\text{mA}$, $T_a=25^\circ\text{C}$ unless otherwise specified)



Typical Performance Characteristics ($V_{OUT}=-1.1V$)

($V_{EE}=V_{OUT}(\text{Typ.})-1V$, $V_{cont}=1.6V$, $I_{OUT}=1\text{mA}$, $T_a=25^\circ\text{C}$ unless otherwise specified)

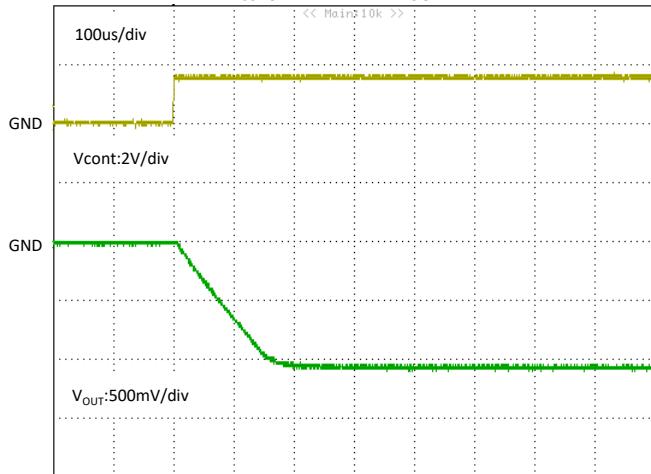


Typical Performance Characteristics ($V_{OUT}=-1.1V$)

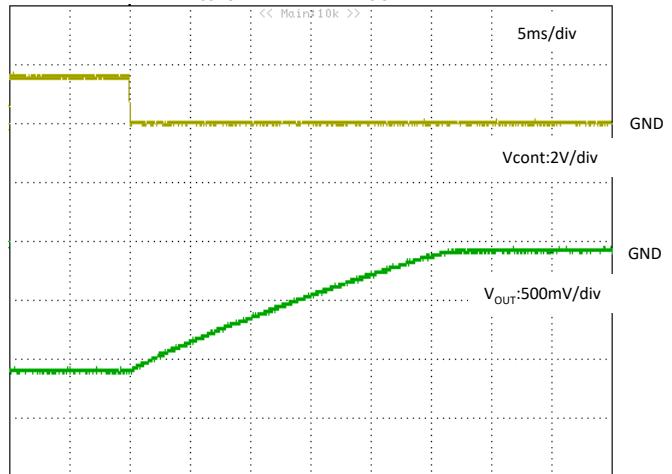
($V_{EE}=V_{OUT}(\text{Typ.})-1V$, $V_{cont}=1.6V$, $I_{OUT}=1\text{mA}$, $T_a=25^\circ\text{C}$ unless otherwise specified)

Cont rise & fall characteristics

$V_{EE}=-2.1V$, $V_{cont}=0 \rightarrow 1.6V$, $I_{OUT}=0\text{mA}$, $C_n=0.01\mu\text{F}$

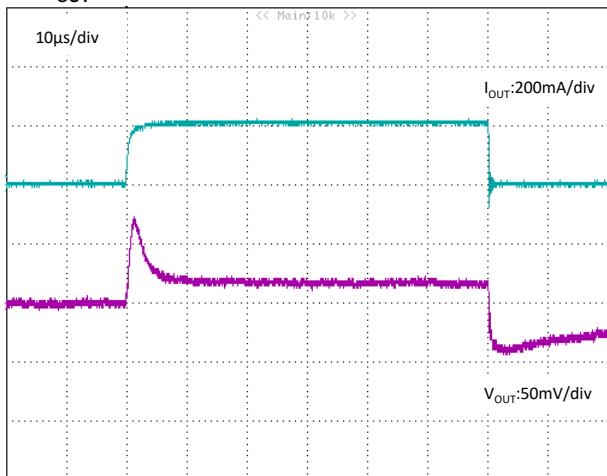


$V_{EE}=-2.1V$, $V_{cont}=1.6 \rightarrow 0V$, $I_{OUT}=0\text{mA}$, $C_n=0.01\mu\text{F}$

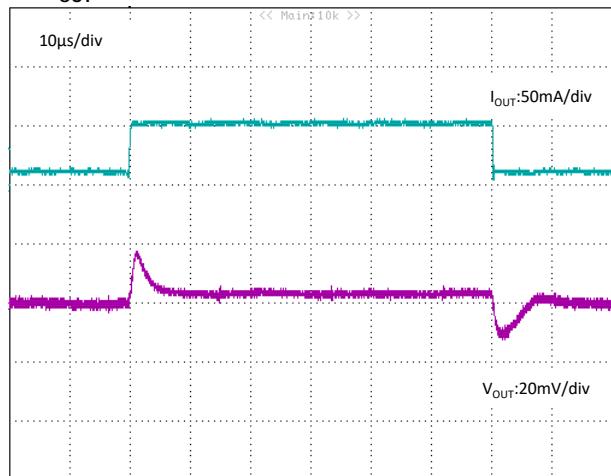


Load transient characteristics

$I_{OUT} : 0.1\text{mA} \leftrightarrow 200\text{mA}$

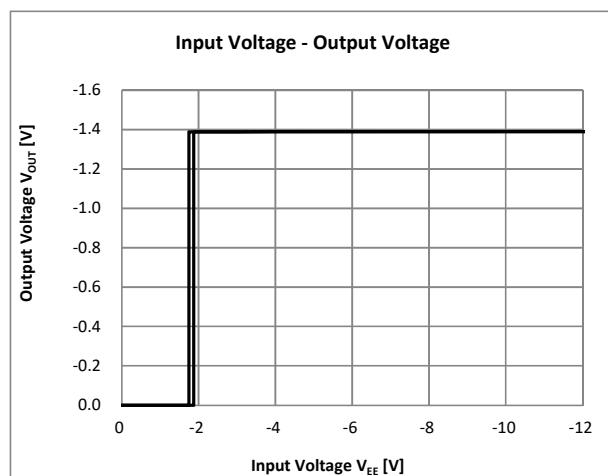
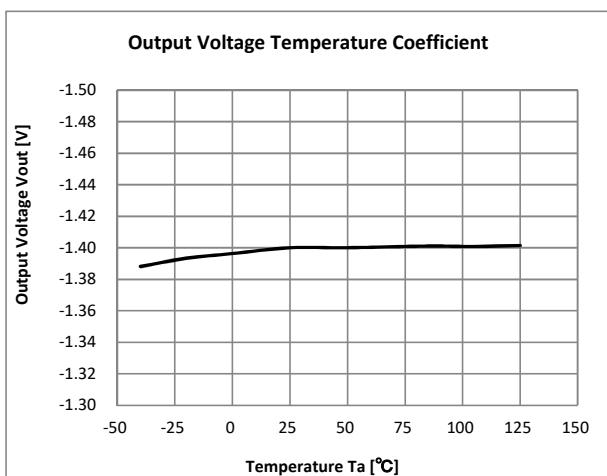
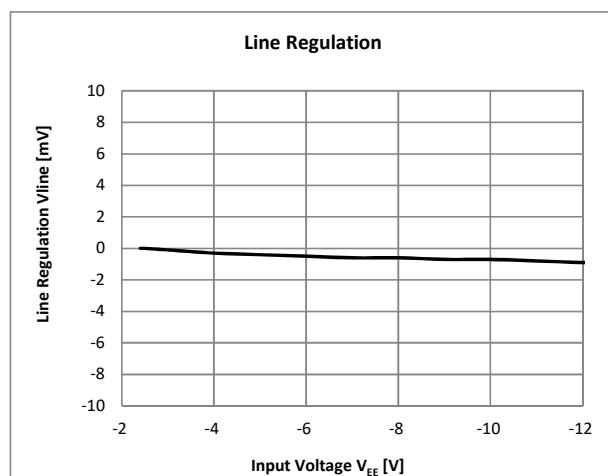
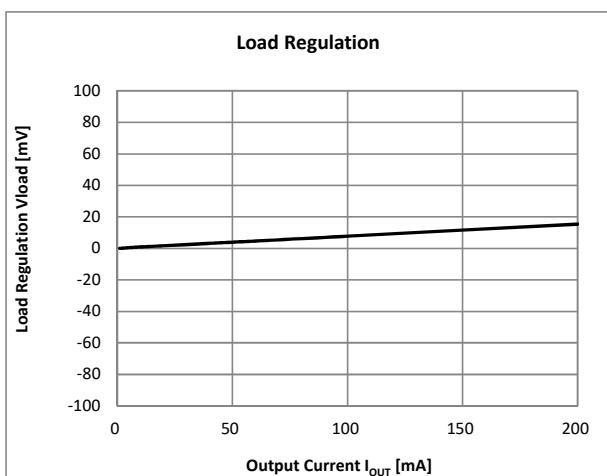
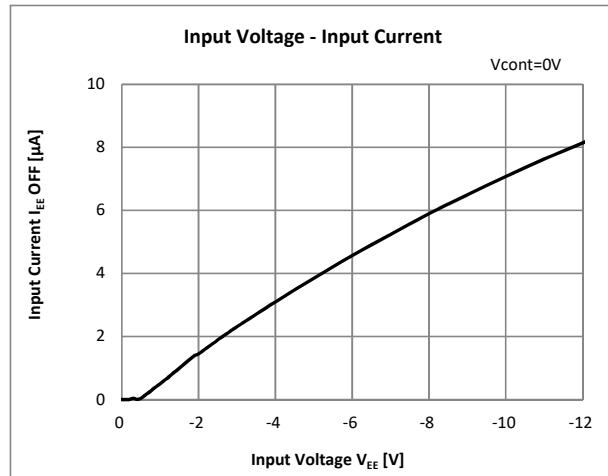
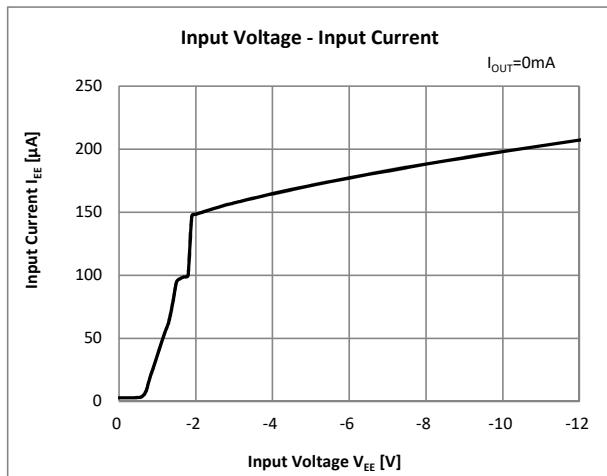


$I_{OUT} : 10\text{mA} \leftrightarrow 50\text{mA}$



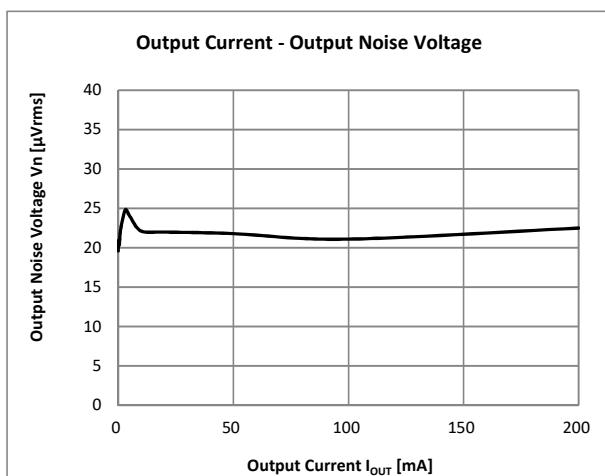
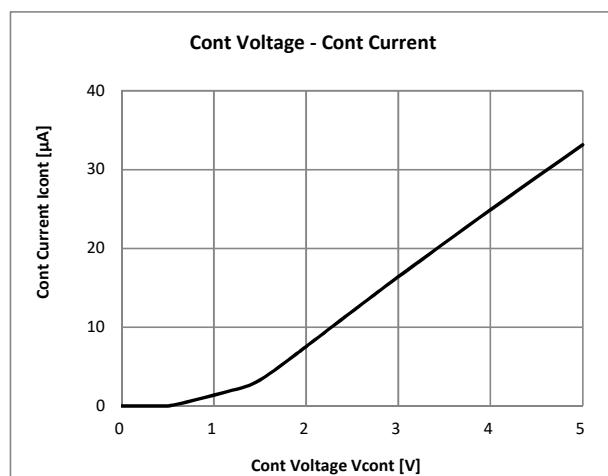
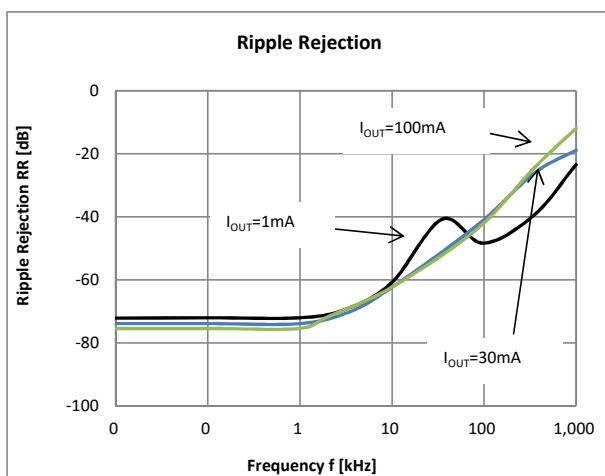
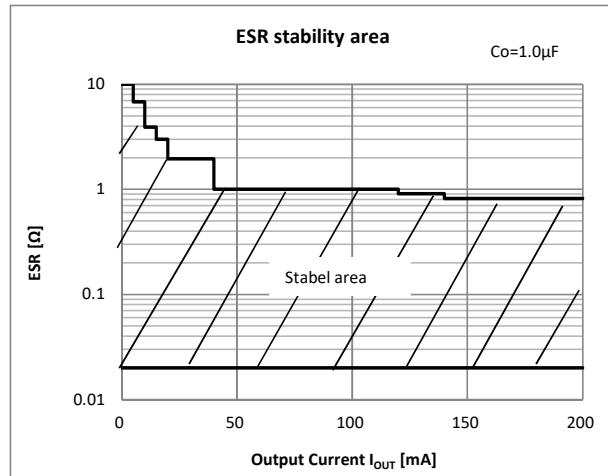
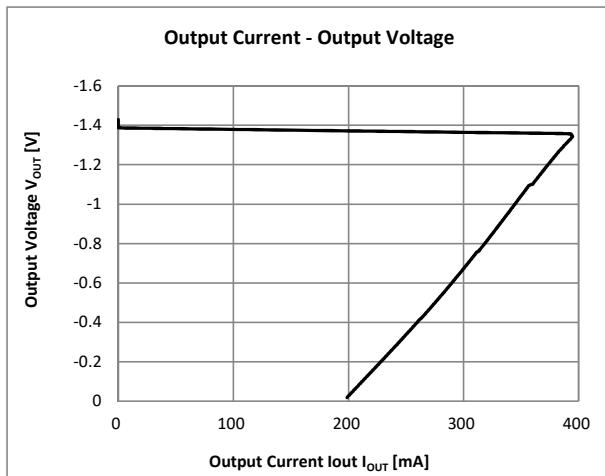
Typical Performance Characteristics ($V_{OUT}=-1.4V$)

($V_{EE}=V_{OUT}(\text{Typ.})-1V$, $V_{cont}=1.6V$, $I_{OUT}=1\text{mA}$, $T_a=25^\circ\text{C}$ unless otherwise specified)



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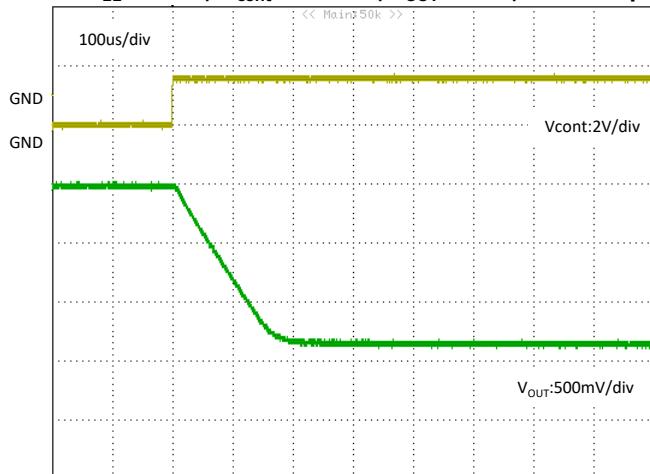


Typical Performance Characteristics ($V_{OUT}=-1.4V$)

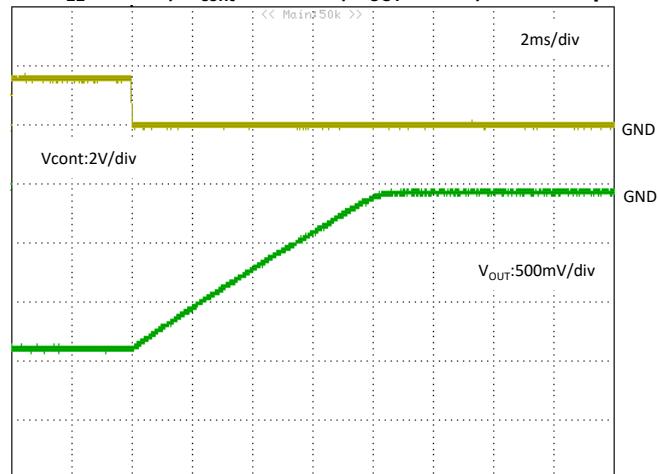
($V_{EE}=V_{OUT}(\text{Typ.})-1V$, $V_{cont}=1.6V$, $I_{OUT}=1\text{mA}$, $T_a=25^\circ\text{C}$ unless otherwise specified)

- Cont rise & fall characteristics

$V_{EE}=-2.4V$, $V_{cont}=0 \rightarrow 1.6V$, $I_{OUT}=0\text{mA}$, $C_n=0.01\mu\text{F}$

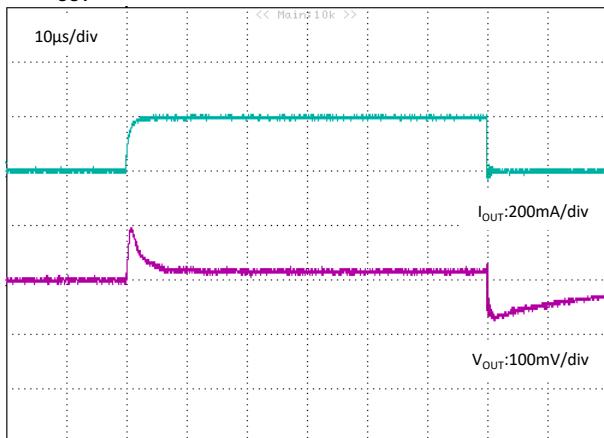


$V_{EE}=-2.4V$, $V_{cont}=1.6 \rightarrow 0V$, $I_{OUT}=0\text{mA}$, $C_n=0.01\mu\text{F}$

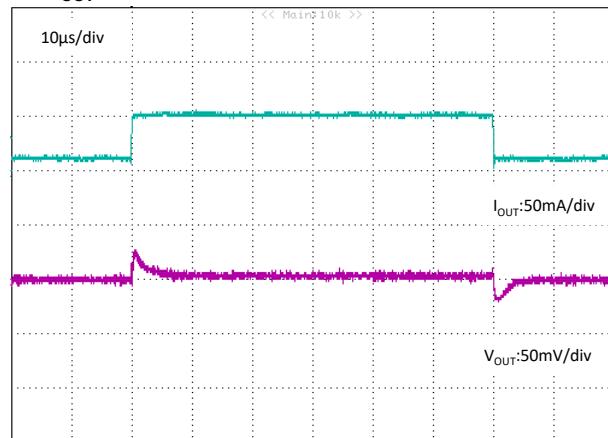


- Load transient characteristics

$I_{out} : 0.1\text{mA} \leftrightarrow 200\text{mA}$

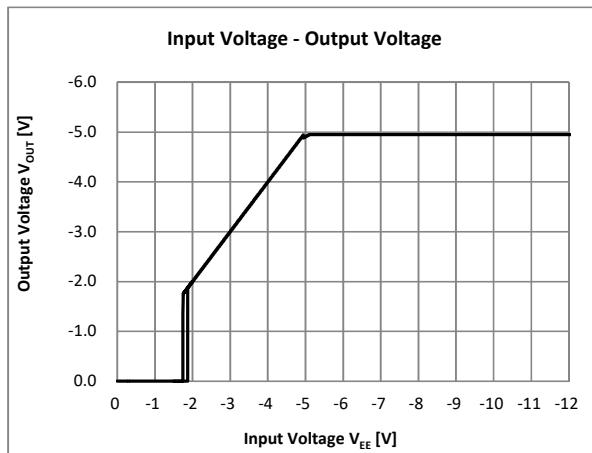
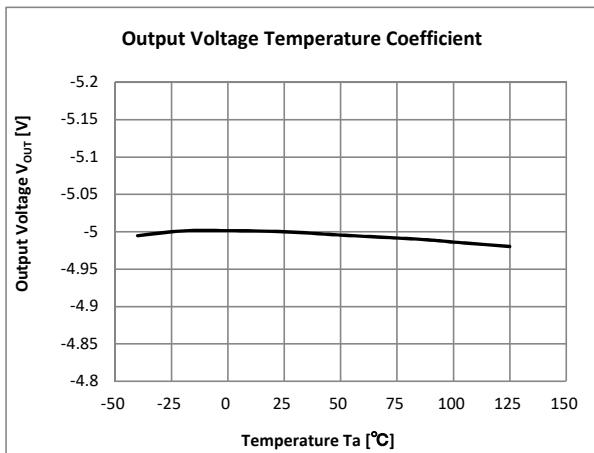
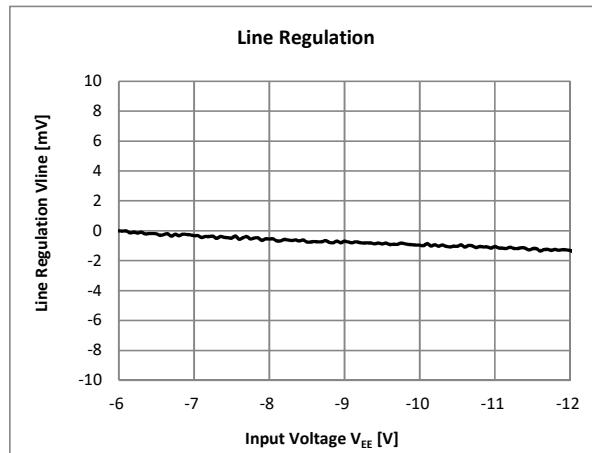
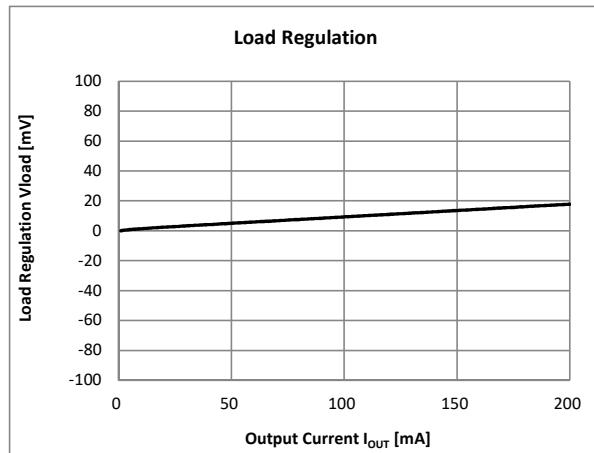
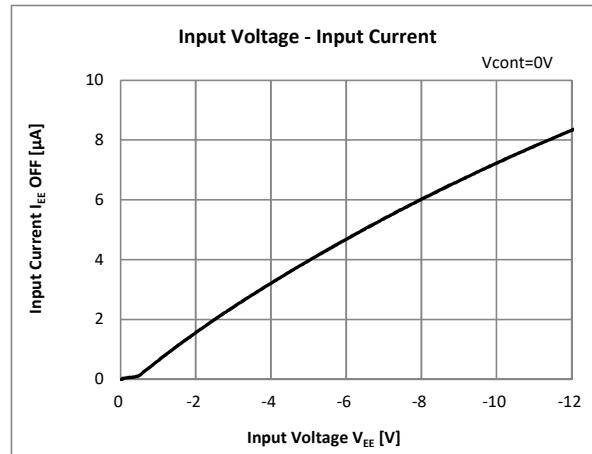
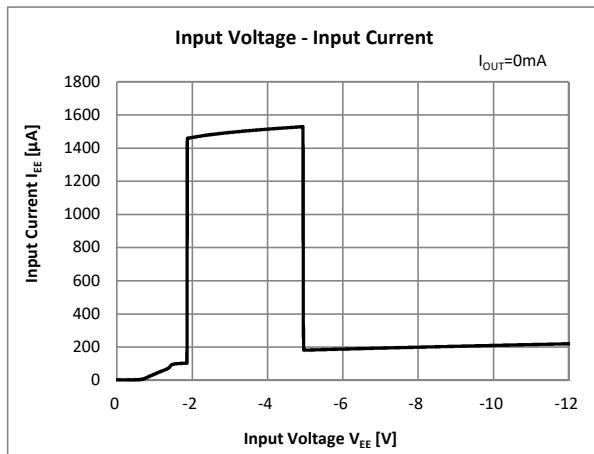


$I_{out} : 10\text{mA} \leftrightarrow 50\text{mA}$



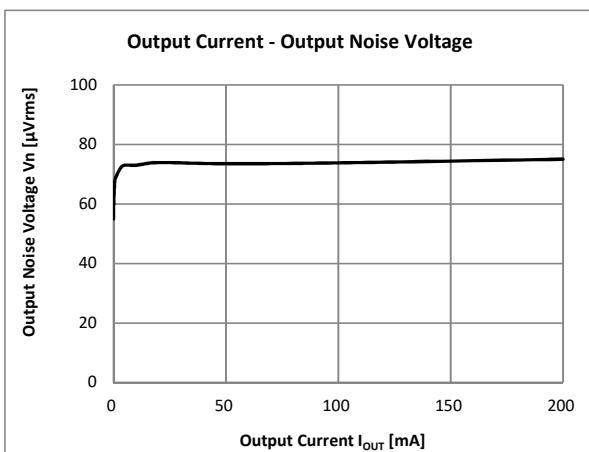
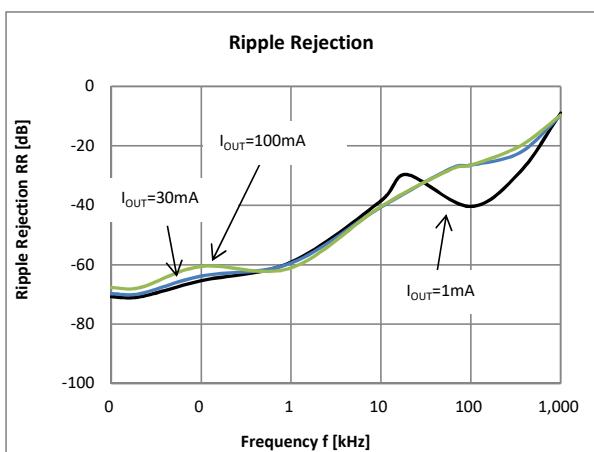
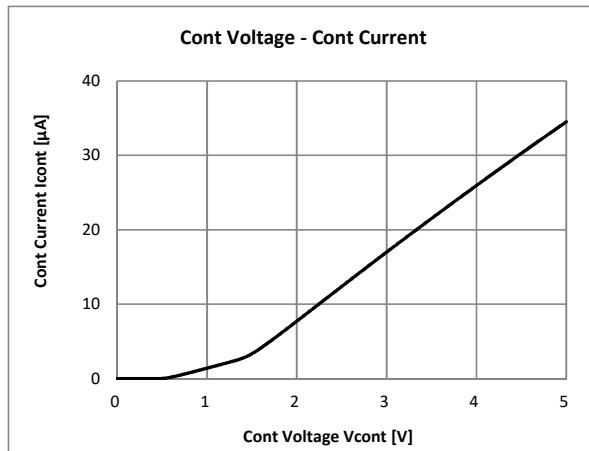
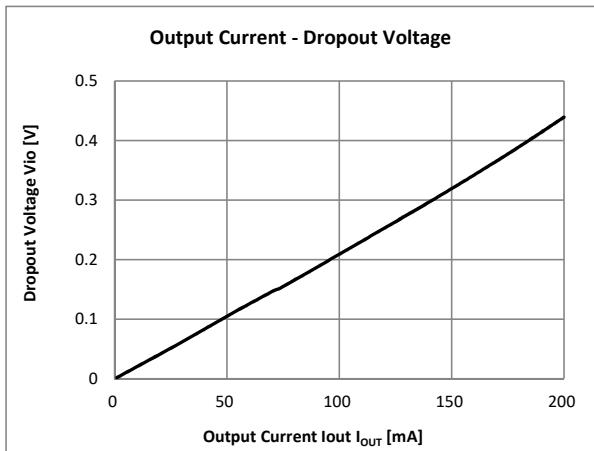
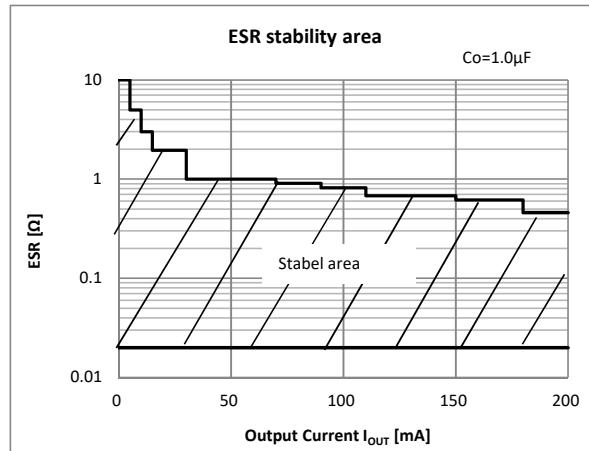
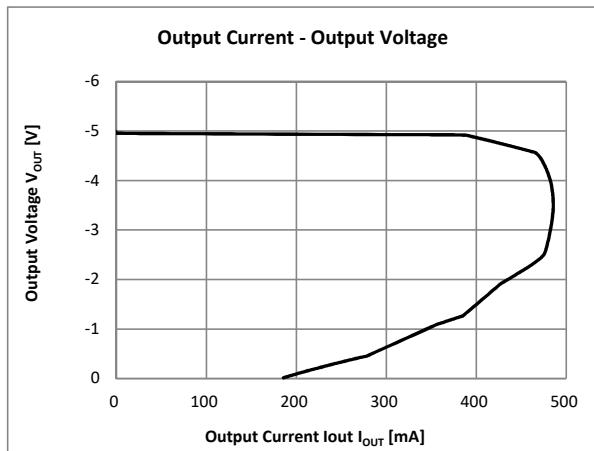
Typical Performance Characteristics ($V_{OUT}=-5.0V$)

($V_{EE}=V_{OUT}(\text{Typ.})-1V$, $V_{cont}=1.6V$, $I_{OUT}=1\text{mA}$, $T_a=25^\circ\text{C}$ unless otherwise specified)



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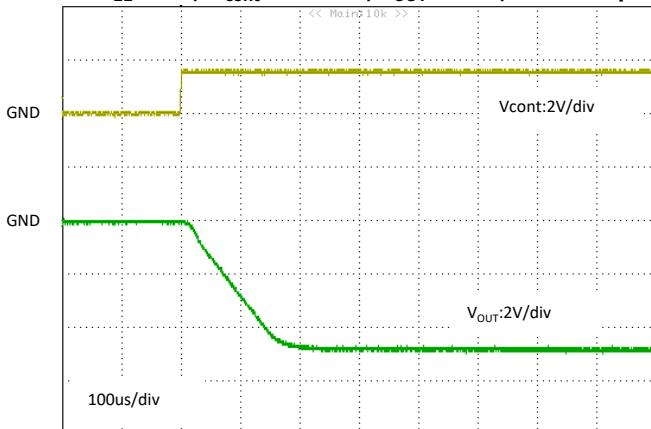


Typical Performance Characteristics ($V_{OUT}=-5.0V$)

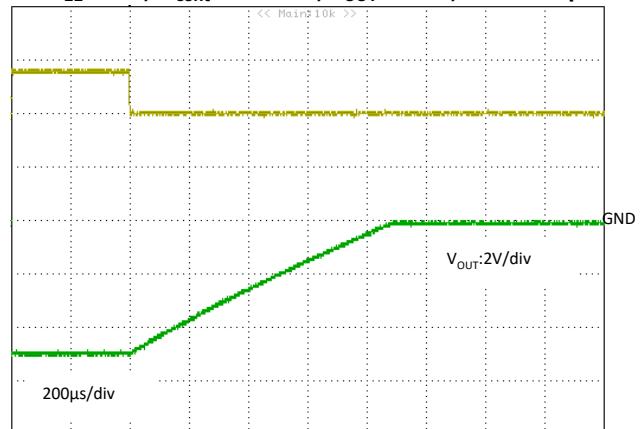
($V_{EE}=V_{OUT}(\text{Typ.})-1V$, $V_{cont}=1.6V$, $I_{OUT}=1\text{mA}$, $T_a=25^\circ\text{C}$ unless otherwise specified)

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$V_{EE}=-6V$, $V_{cont}=0 \rightarrow 1.6V$, $I_{OUT}=0\text{mA}$, $C_n=0.01\mu\text{F}$

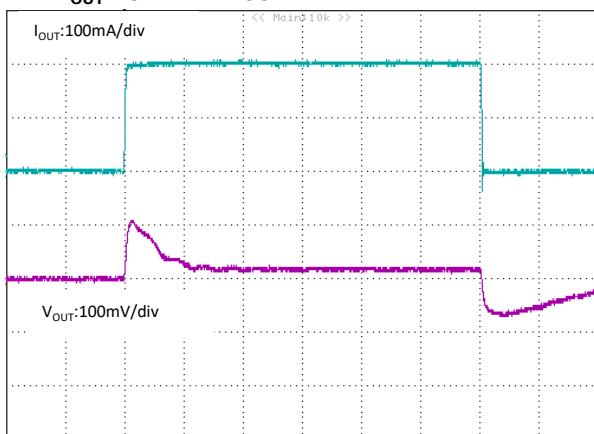


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